Low-Voltage CMOS Octal Buffer

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX244 is a high performance, non-inverting octal buffer operating from a 2.3 to 5.5 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX244 inputs to be safely driven from 5 V devices. The MC74LCX244 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable (\overline{OE}) input, when HIGH, disables the output by placing them in a HIGH Z condition.

Features

- Designed for 2.3 to 5.5 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- · Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When V_{CC} = 0 V
- LVTTL Compatible
- · LVCMOS Compatible
- · 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ◆ Human Body Model >2000 V
 - ◆ Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

www.onsemi.com





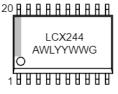


SOIC-20 WB DW SUFFIX CASE 751D

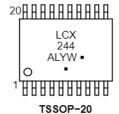
TSSOP-20 DT SUFFIX CASE 948E

QFN20 MN SUFFIX CASES 485AA & 485CB

MARKING DIAGRAMS



SOIC-20 WB



1 O LCX 244 ALYW•



QFN20 - 485AA

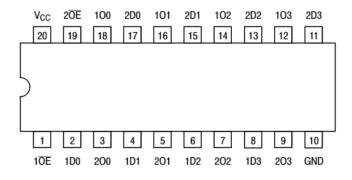
QFN20 - 485CB

A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.



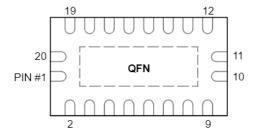


Figure 1. Pinouts: 20-Lead (Top View)

PIN NAMES

PINS	FUNCTION
nŌĒ	Output Enable Inputs
1Dn, 2Dn	Data Inputs
10n, 20n	3-State Outputs

TRUTH TABLE

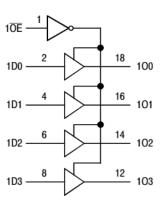
INP	UTS	OUTPUTS
10E 20E	1Dn 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	Х	Z

H = High Voltage Level

L = Low Voltage Level

Z = High Impedance State X = High or Low Voltage Level and Transitions are Acceptable

For I_{CC} reasons, DO NOT FLOAT Inputs



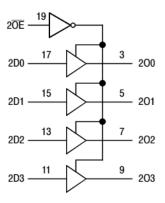


Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
IoK	DC Output Diode Current	-50	V _O < GND	mA
		+50	Vo>Vcc	mA
I _O	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	T _L = 260		°C
TJ	Junction Temperature Under Bias	T _J = 150		°C
θ_{JA}	Thermal Resistance (Note 2)	θ _{JA} = 140		°C/W
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	5.5 5.5	V
VI	Input Voltage	0		5.5	V
Vo	Output Voltage HIGH or LOW State 3-State	0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			-24 -12	mA
I _{OL}	LOW Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V			24 12	mA
TA	Operating Free-Air Temperature	-55		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

I_O absolute maximum rating must be observed.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

DC ELECTRICAL CHARACTERISTICS

			T _A = -55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Units
V _{IH}	HIGH Level Input Voltage (Note 3)	2.3 V ≤ V _{CC} ≤ 2.7 V	1.7		V
		2.7 V ≤ V _{CC} ≤ 3.6 V	2.0		1
V _{IL}	LOW Level Input Voltage (Note 3)	2.3 V ≤ V _{CC} ≤ 2.7 V		0.7	V
		2.7 V ≤ V _{CC} ≤ 3.6 V		0.8	1
V _{OH}	HIGH Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OL} = 100 \mu\text{A}$	V _{CC} - 0.2		V
		V _{CC} = 2.3 V; I _{OH} = -8 mA	1.8]
		$V_{CC} = 2.7 \text{ V; } I_{OH} = -12 \text{ mA}$	2.2]
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -18 \text{ mA}$	2.4]
		$V_{CC} = 3.0 \text{ V; } I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	$2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{ I}_{OL} = 100 \mu\text{A}$		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.6	
		$V_{CC} = 2.7 \text{ V}; I_{OL} = 12 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; I_{OL} = 16 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V; } I_{OL} = 24 \text{ mA}$		0.55	
I _{OZ}	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5	μА
I _{OFF}	Power Off Leakage Current	V _{CC} = 0, V _{IN} = 5.5 V or V _{OUT} = 5.5 V		10	μА
I _{IN}	Input Leakage Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		±5	μА
Icc	Quiescent Supply Current	V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND		10	μА
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$		500	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}$; $R_L = 500 \Omega$)

					Lin	nits			
					T _A = -55°C	to +125°C] !
			V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.	5 V ± 0.2] !
			C _L =	50 pF	C _L = 9	50 pF	C _L = 3	30 pF] !
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	1.5 1.5	7.8 7.8	ns
t _{PZH}	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	10 10	ns
t _{PHZ}	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	1.5 1.5	8.0 8.0	1.5 1.5	8.4 8.4	ns
toshl toslh	Output-to-Output Skew (Note 4)			1.0 1.0					ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

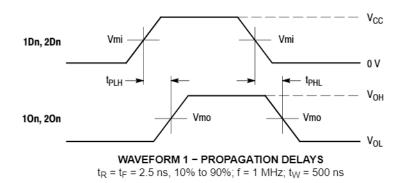
			Т	T _A = +25°C	:	
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 5)	$\begin{array}{c} V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{array}$		0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 5)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		-0.8 -0.6		V

^{5.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

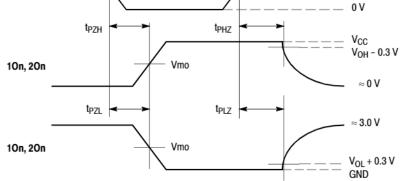
^{3.} These values of V_I are used to test DC electrical characteristics only.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V _{CC} = 3.3 V, V _I = 0 V or V _{CC}	25	pF



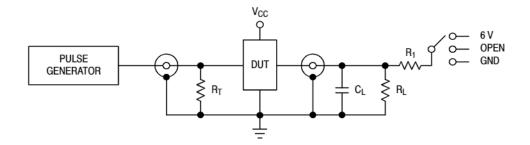
Vmi Vmi 0 V



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

Figure 3. AC Waveforms

	V _{CC}				
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V		
Vmi	1.5 V	1.5 V	V _{CC} /2		
Vmo	1.5 V	1.5 V	V _{CC} /2		
V _{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V		
V _{LZ}	V _{OH} - 0.3 V	V _{OH} - 0.3 V	V _{OH} - 015 V		



TEST	switch
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at V _{CC} = 3.3 ± 0.3 V 6 V at V _{CC} = 2.5 ± 0.2 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

 C_L = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance)

 $C_L=30$ pF at $V_{CC}=2.5\pm0.2$ V or equivalent (includes jig and probe capacitance) $R_L=R_1=500$ Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

ORDERING INFORMATION

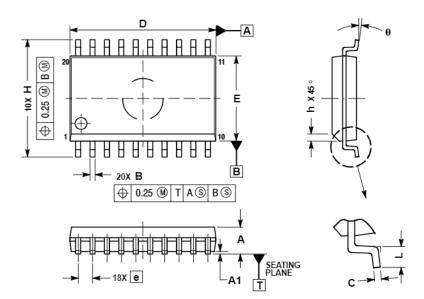
Device	Package	Shipping [†]
MC74LCX244DWG	SOIC-20 WB (Pb-Free)	38 Units / Rail
MC74LCX244DWR2G	SOIC-20 WB (Pb-Free)	1000 / Tape & Reel
MC74LCX244DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LCX244DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
NLV74LCX244DTR2G*	TSSOP-20 (Pb-Free)	2500 / Tape & Reel
MC74LCX244MNTWG	QFN20, 2.5x4.5 (Pb-Free)	3000 / Tape & Reel
MC74LCX244MN2TWG	QFN20, 2.5x3.5 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

PACKAGE DIMENSIONS

SOIC-20 WB CASE 751D-05 ISSUE H

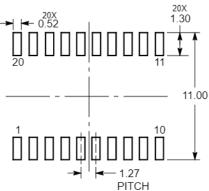


NOTES:

- OTES:
 DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
 PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION
 SHALL BE 0.13 TOTAL IN EXCESS OF B
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	h 0.25 (
L	0.50	0.90			
θ	0°	7°			

RECOMMENDED **SOLDERING FOOTPRINT***

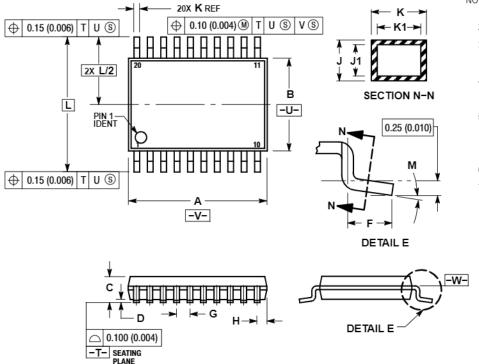


DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-20 CASE 948E ISSUE D



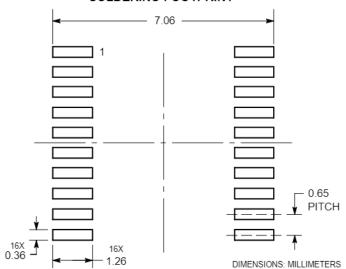
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
 MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS, MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION, INTERLEAD FLASH OR PROTRUSION, INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W.

 MILLIMETERS INCHES

ZETERMINIED ZU DZ U OM T ETUE T					
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0°	8°	0°	8°	

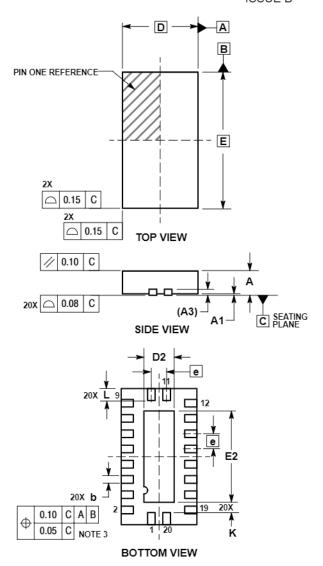
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

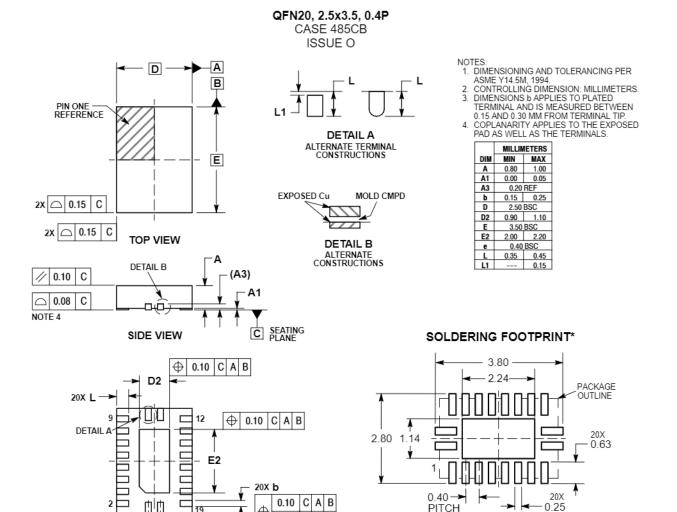
QFN20, 2.5x4.5 MM CASE 485AA ISSUE B



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.80	1.00	
A1	0.00	0.05	
A3	0.20 REF		
b	0.20	0.30	
D	2.50 BSC		
D2	0.85	1.15	
E	4.50 BSC		
E2	2.85	3.15	
е	0.50 BSC		
K	0.20		
L	0.35	0.45	

PACKAGE DIMENSIONS



Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and a retrademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications using ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semicond

0.05 C NOTE 3

PUBLICATION ORDERING INFORMATION

е

BOTTOM VIEW

e/2

LITERATURE FULFILLMENT

0

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative